sPHENIX INTT -Beam Test 2021

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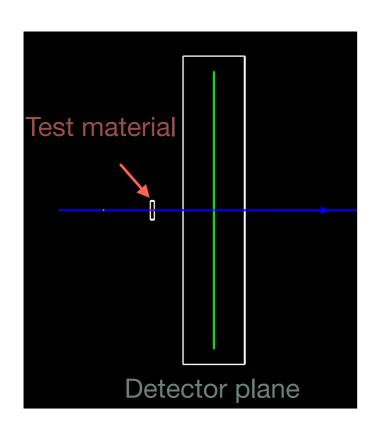




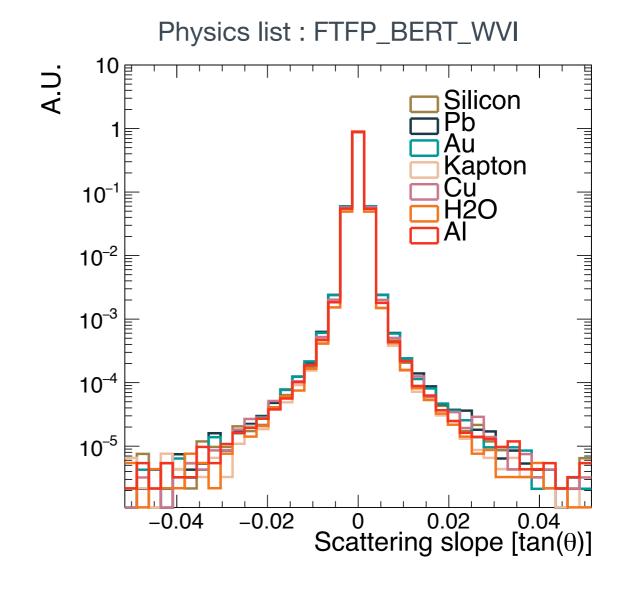


Physics list test - FTFP_BERT_WVI





	radiation length (cm)	thickness (um)
Silicon	9.370	320.000
Lead Pb	0.5612	19.166
Gold Au	0.3344	11.420
Kapton	28.57	975.710
cooper Cu	1.436	49.042
water	36.08	1232.188
Aluminum	8.897	303.846



The distributions are quite similar to each other

Possibility of simulating charge sharing



Hello Cheng-Wei,

Reply from the tracking group about the charge sharing

ln:

https://github.com/sPHENIX-

Collaboration/coresoftware/blob/master/simulation/g4simulation/g4intt/PHG4InttHitReco.cc

lines 284-397 is an attempt to mimic charge sharing. The diffusion was just made up without any real basis, so you could try changing that.

Let me know if you have querstions.

Best regards

Tony

178	// Intt digitization		المنا طبيطة		
179	Github lin				
180	// these should be used for the Intt				
181	/*				
182	How threshold are calculated based on default FPHX settings				
183	Four part information goes to the threshold calculation:				
184	1. In 320 um thick silicon, the MIP e-h pair for a nominally indenting tracking is 3.87 MeV/cm st 320 um $/$ 3.				
185	2. From DOI: 10.1016/j.nima.2014.04.017, FPHX integrator amplifier gain is 100mV / fC. That translate MIP vo				
186	3. From [FPHX Final Design Document](https://www.phenix.bnl.gov/WWW/fvtx/DetectorHardware/FPHX/FPHX2_June200				
187	4, From [FPHX Final Design Document](https://www.phenix.bnl.gov/WWW/fvtx/DetectorHardware/FPHX/FPHX2_June200				
188					
189	FPHX Register Address Name	Default value Voltage -	Vref (mV) To electrons based on cali		
190					
191		DAC 0 8 32	2500		
192	5 Threshol		5000		
193	6 Threshol		10000		
194	7 Threshol		15000		
195	8 Threshol		25000		
196	9 Threshol		35000		
197	10 Threshol		45000		
198		DAC 7 176 704	55000		
199		ovoltage are set to PHG4InttDigitiz	er::set_adc_scale as 3-bit ADC thresho		
200	*/				

Backup